

## Silicon NPN Power Transistors

2SC3083

## DESCRIPTION

- With TO-3PN package
- High breakdown voltage ( $V_{CBO} \geq 500V$ )
- Fast switching speed
- Wide ASO ( Safe Operating Area )

## APPLICATIONS

- 400V/6A switching regulator applications

## PINNING

| PIN | DESCRIPTION                          |
|-----|--------------------------------------|
| 1   | Base                                 |
| 2   | Collector;connected to mounting base |
| 3   | Emitter                              |

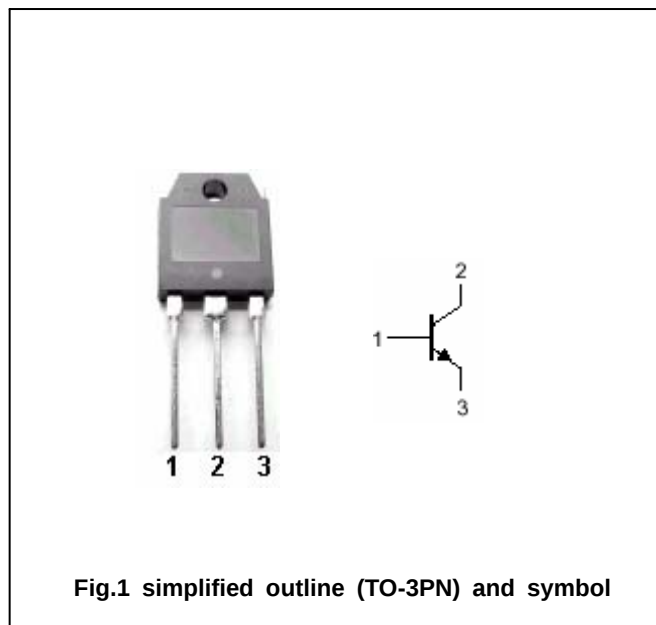


Fig.1 simplified outline (TO-3PN) and symbol

Absolute maximum ratings ( $T_a=25^\circ C$ )

| SYMBOL    | PARAMETER                   | CONDITIONS     | VALUE   | UNIT |
|-----------|-----------------------------|----------------|---------|------|
| $V_{CBO}$ | Collector-base voltage      | Open emitter   | 500     | V    |
| $V_{CEO}$ | Collector-emitter voltage   | Open base      | 400     | V    |
| $V_{EBO}$ | Emitter-base voltage        | Open collector | 7       | V    |
| $I_C$     | Collector current           |                | 6       | A    |
| $I_{CM}$  | Collector current-peak      |                | 12      | A    |
| $I_B$     | Base current                |                | 2       | A    |
| $P_C$     | Collector power dissipation | $T_a=25$       | 2.5     | W    |
|           |                             | $T_C=25$       | 60      |      |
| $T_j$     | Junction temperature        |                | 150     |      |
| $T_{stg}$ | Storage temperature         |                | -55~150 |      |

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## CHARACTERISTICS

T<sub>j</sub>=25 unless otherwise specified

| SYMBOL               | PARAMETER                            | CONDITIONS                                        | MIN | TYP. | MAX | UNIT |
|----------------------|--------------------------------------|---------------------------------------------------|-----|------|-----|------|
| V <sub>(BR)CEO</sub> | Collector-emitter breakdown voltage  | I <sub>C</sub> =5mA ; R <sub>BE</sub> =∞          | 400 |      |     | V    |
| V <sub>(BR)CBO</sub> | Collector-base breakdown voltage     | I <sub>C</sub> =1mA ; I <sub>E</sub> =0           | 500 |      |     | V    |
| V <sub>(BR)EBO</sub> | Emitter-base breakdown voltage       | I <sub>E</sub> =1mA ; I <sub>C</sub> =0           | 7   |      |     | V    |
| V <sub>CEsat</sub>   | Collector-emitter saturation voltage | I <sub>C</sub> =2A ; I <sub>B</sub> =0.4A         |     |      | 1.0 | V    |
| V <sub>BEsat</sub>   | Base-emitter saturation voltage      | I <sub>C</sub> =2A ; I <sub>B</sub> =0.4A         |     |      | 1.5 | V    |
| I <sub>CBO</sub>     | Collector cut-off current            | V <sub>CB</sub> =400V ; I <sub>E</sub> =0         |     |      | 10  | μA   |
| I <sub>EBO</sub>     | Emitter cut-off current              | V <sub>EB</sub> =5V ; I <sub>C</sub> =0           |     |      | 10  | μA   |
| h <sub>FE-1</sub>    | DC current gain                      | I <sub>C</sub> =0.4A ; V <sub>CE</sub> =5V        | 15  |      | 50  |      |
| h <sub>FE-2</sub>    | DC current gain                      | I <sub>C</sub> =2A ; V <sub>CE</sub> =5V          | 8   |      |     |      |
| C <sub>OB</sub>      | Output capacitance                   | I <sub>E</sub> =0 ; V <sub>CB</sub> =10V ; f=1MHz |     | 40   |     | pF   |
| f <sub>T</sub>       | Transition frequency                 | I <sub>C</sub> =0.4A ; V <sub>CE</sub> =10V       |     | 20   |     | MHz  |

## Switching times

|                 |              |                                                                                                              |  |  |     |    |
|-----------------|--------------|--------------------------------------------------------------------------------------------------------------|--|--|-----|----|
| t <sub>on</sub> | Turn-on time | I <sub>C</sub> =3A ; I <sub>B1</sub> =-I <sub>B2</sub> =0.6A<br>R <sub>L</sub> =66.6Ω, V <sub>CC</sub> =200V |  |  | 1.0 | μs |
| t <sub>s</sub>  | Storage time |                                                                                                              |  |  | 2.5 | μs |
| t <sub>f</sub>  | Fall time    |                                                                                                              |  |  | 1.0 | μs |

◆ h<sub>FE-1</sub> classifications

| L     | M     | N     |
|-------|-------|-------|
| 15-30 | 20-40 | 30-50 |

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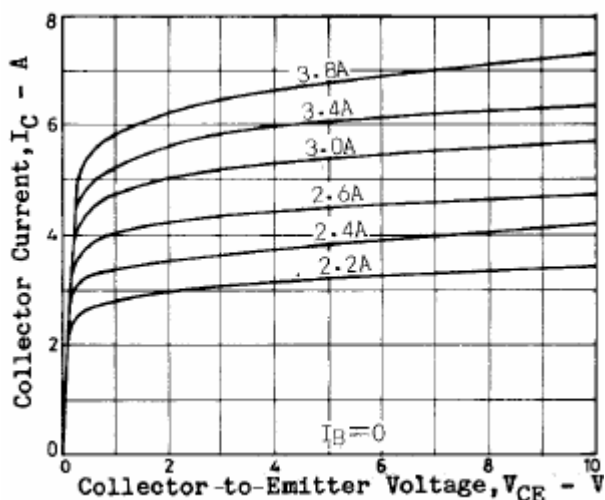


Fig.3 Static Characteristic

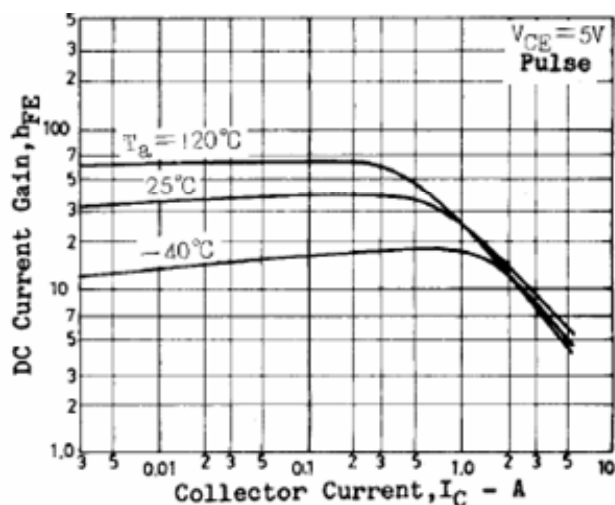


Fig.4 DC current Gain

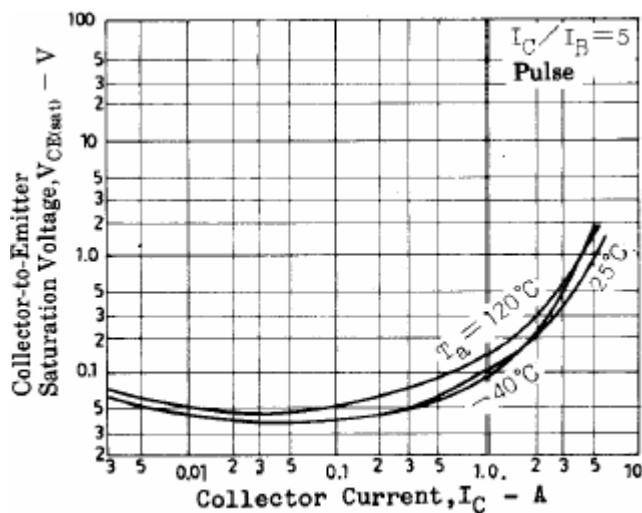


Fig.5 Collector-Emitter Saturation Voltage

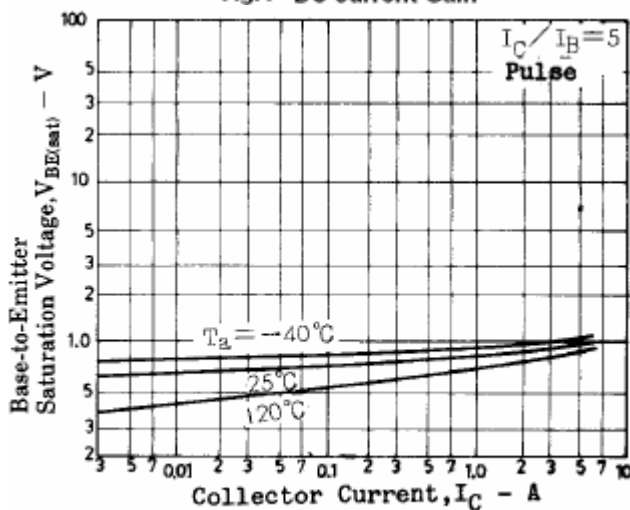


Fig.6 Base-Emitter Saturation Voltage

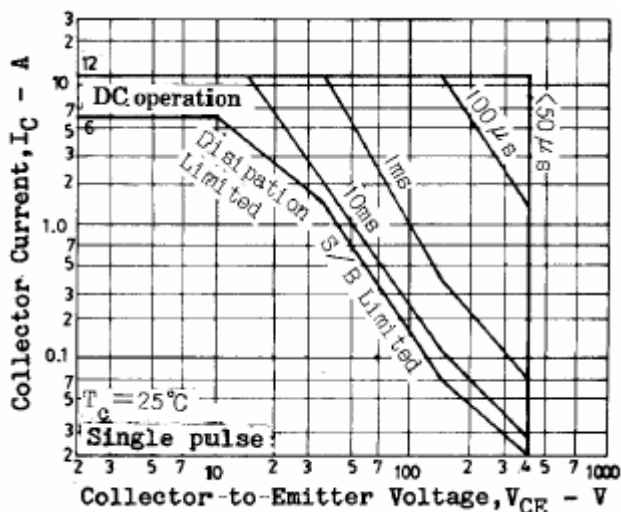


Fig.7 Safe Operating Area